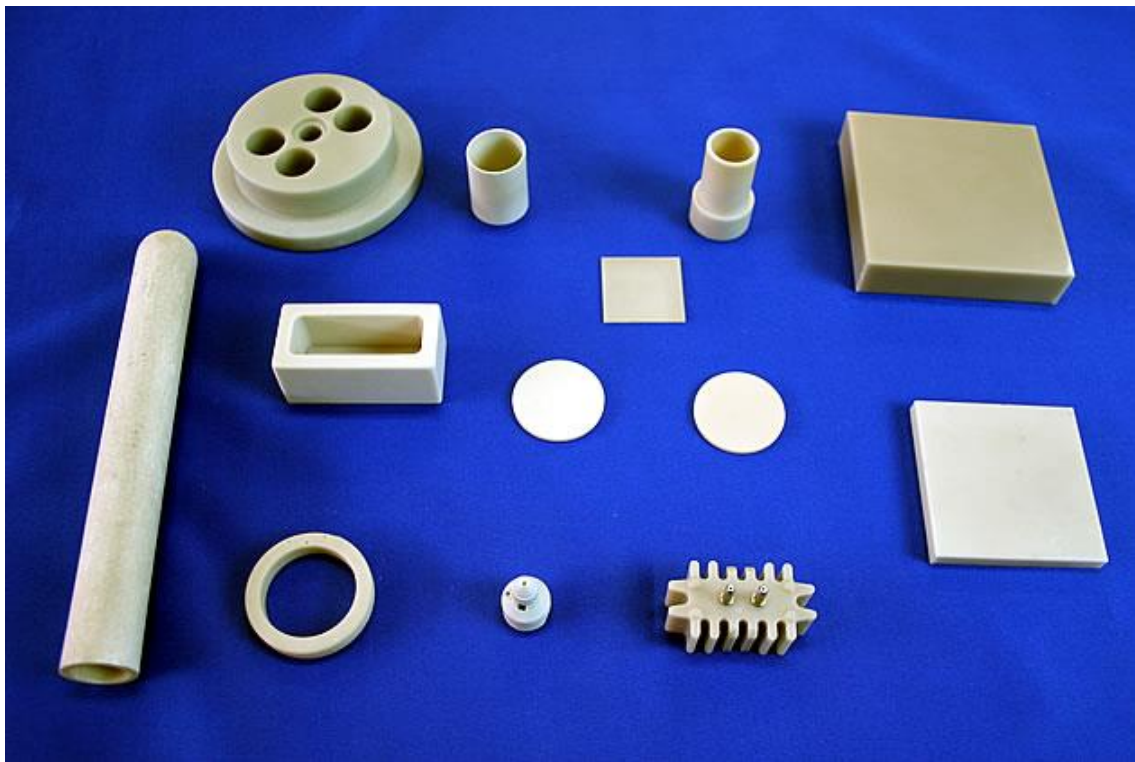


Nishimura Aluminum Nitride



-ALN-170 High thermal conductivity(170W)

-ALN-HY0 High purity

Character

: ALN material has good thermal conductivity, heat radiation, and electric insulation. Also it has great thermal shock resistance.

Thermal expansion go well with a Silicon wafer.

Good corrosion resistance to fluorine-containing gases.

Good plasma resistance.

Shape

: Plate, rod, pipe...Any kind of shape is acceptable.

Manufacturing method : Pressing, injection molding, CIP, or Green processing

Usefulness

: ALN material is used for heat sink, base plate, soaking plate for heater, crucible, and a parts for semiconductor devices(CVD, etching, so on..)

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Nishimura Aluminum Nitride



Usefulness : Susceptor, Electro static chucks, Vacuum chucks for heater soaking board, heater, dummy wafer, sputtering target, and so on.

Size : ~ ϕ / \square 550mm
 Thickness 0.25 ~ 30mm

ALN material Propertie		Nsihimura Aluminum nitride	
		ALN-170	ALN-HYO
Thermal conductivity	W/m · K(RT)	170	90
Heat radiation	(100°C)	0.93	0.93
Thermal expansion coefficient	$10^{-6}/^{\circ}\text{C}$ (RT~400°C)	4.5	4.5
Insulation resistance	$\Omega \cdot \text{cm}$ (RT)	$>10^{13}$	$>10^{13}$
Dielectric voltage	kV/mm(RT)	15	15
Dielectric constant	(1MHz)	8.8	8.8
Dielectric loss	10^{-4} (1MHz)	5	5
Bending strength	kgf/mm ²	35	40
Density	g/cm ³	3.32	3.23
Yttria	%	3.5	0
Oxygen	%	1.5	0.58
Metallic impurity	ppm	<500	<500